

Memory Product Specification

78.B1GMA.AF20B

4GB 512M x 64

DDR4-2400MHz CL16 Overclocking Unbuffered DIMM

Description:

The overclocking unbuffered Module for 512M x 64 of 4GB DDR4-2400MHz CL16-16-16-36 at 1.2V Memory Module.

The Module base on eight 512M x 8 DDR4 FBGA SDRAM components.

The SPDs are programmed to JEDEC standard latency DDR4-2133MHz of CL15-15-15-33 at 1.2V.

Memory Module intended for mounting into 288-pin edge connector sockets.

The electrical and mechanical specifications are as follows:

Features:

- DDR4 Speed Grade : 2133Mbps
- Organization
 - 512M × 64, 1 rank
- Mounting 8 pieces of 4G bits DDR4 SDRAM sealed in FBGA
- Package: 288-pin socket type dual in-line memory module (DIMM)
 - PCB height: 1.230 inch (31.25 mm)
 - Lead-free (RoHS compliant)
 - Halogen free
- Power supply: VDD = 1.2V (1.14V to 1.26V)
- 16 internal banks (4 Bank Groups)
- Burst lengths (BL): 8 and 4 with Burst Chop (BC)
- Precharge: auto precharge option for each burst access
- Refresh: auto-refresh, self-refresh

- Refresh cycles
 - Average refresh period
 - 7.8 μ s at 0°C $\leq$ TC $\leq$ +85°C
 - 3.9 μ s at +85°C < TC $\leq$ +95°C
- Operating case temperature range
 - TC = 0°C to +95°C

Overclocking Datasheet w/ Intel XMP:

- DDR4 Speed Grade : 2400Mbps
- Power supply: VDD Voltage : 1.2V
VDDQ Voltage: 1.2V
- CAS latency : CL16-16-16-36
- Bandwidth : 19200MB/s
- Serial presence detect with EEPROM.
- PCB height : 1.230 inch (31.25 mm)
- RoHS Compliant
- Halogen free
- Application : Gaming player

Dimensions